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**Rui et al.**

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(54) **HYBRID HIGH-K DIELECTRIC MATERIAL FILM STACKS COMPRISING ZIRCONIUM OXIDE UTILIZED IN DISPLAY DEVICES**

(58) **Field of Classification Search**  
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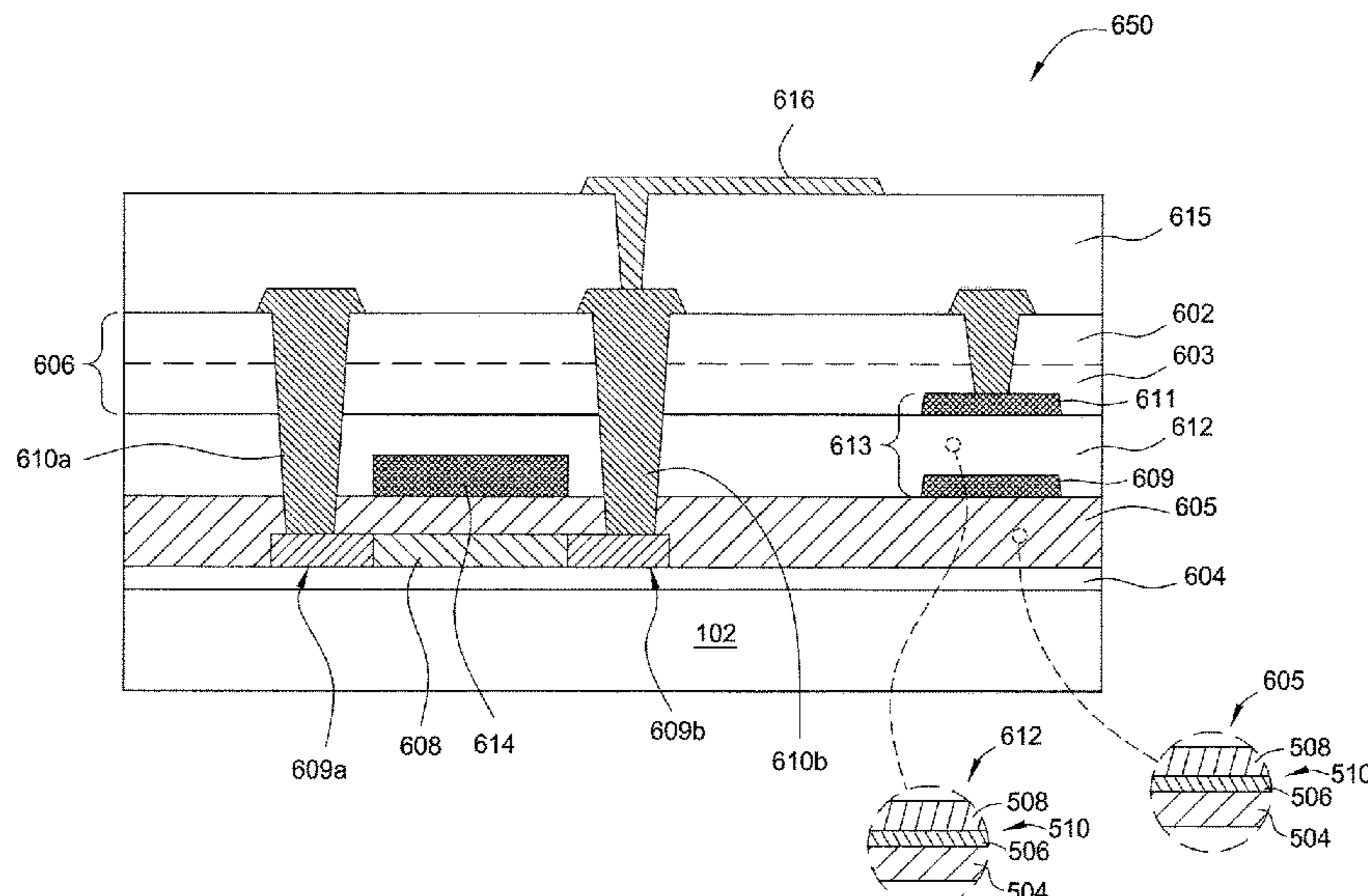
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(57) **ABSTRACT**

Embodiments of the disclosure generally provide methods of forming a hybrid film stack that may be used as a capacitor layer or a gate insulating layer with a high dielectric constant as well as film qualities for display applications. In one embodiment, a thin film transistor structure include gate, source and drain electrodes formed on a substrate, and an insulating layer formed on a substrate, wherein the insulating layer is a hybrid film stack having a dielectric layer comprising a zirconium containing material disposed on an interface layer formed above or below the gate, source and drain electrodes.

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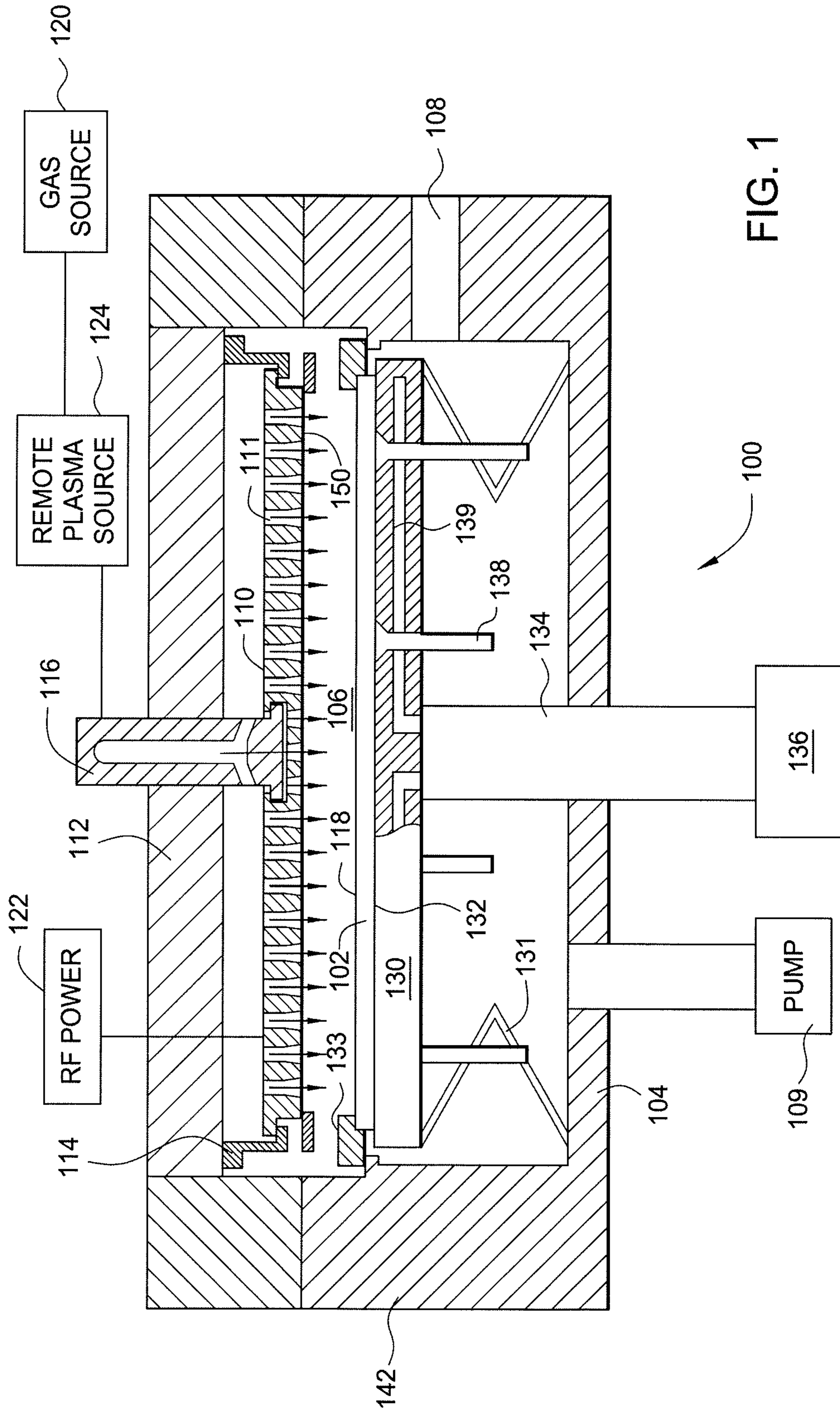
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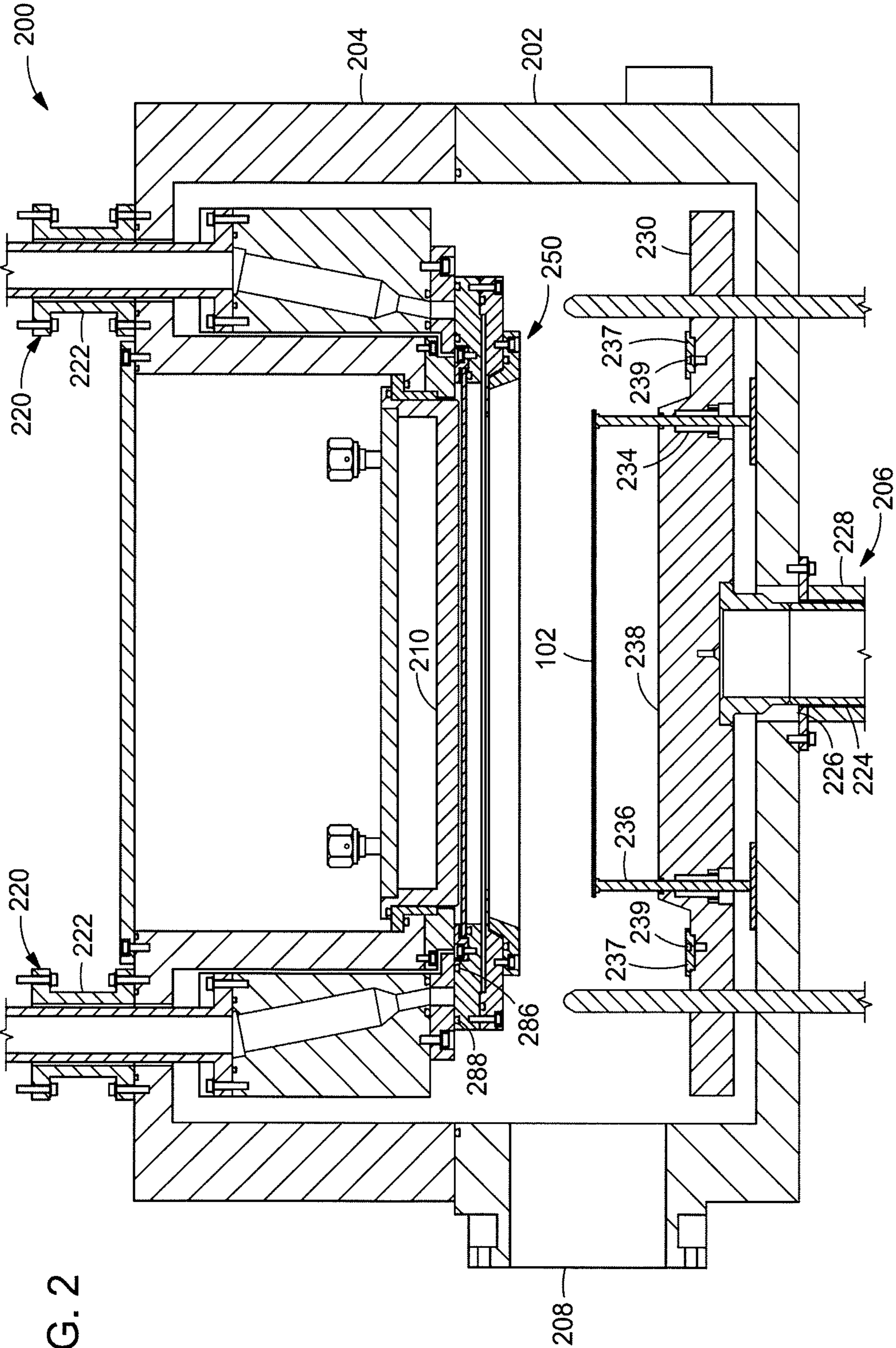


FIG. 2

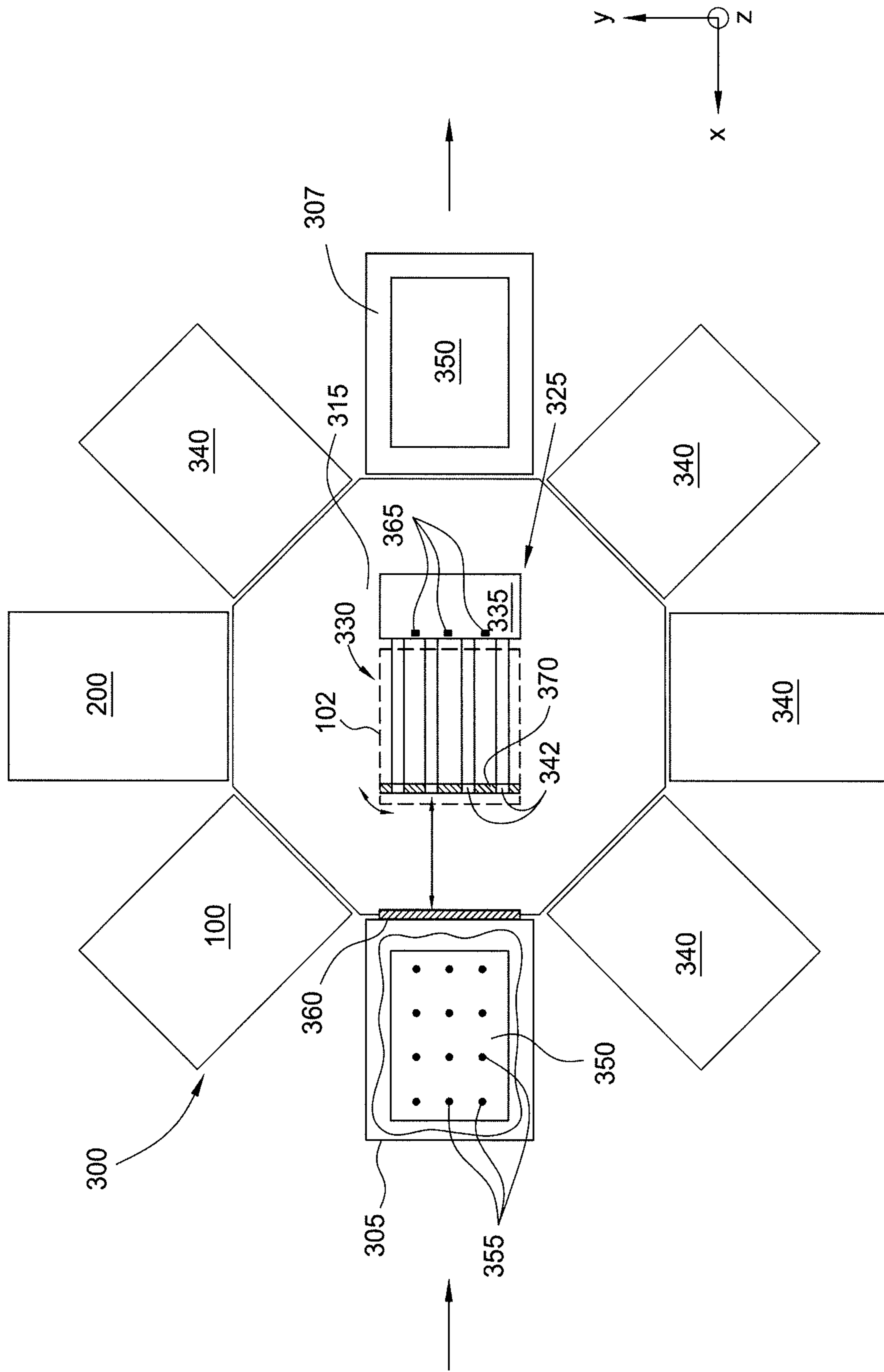


FIG. 3

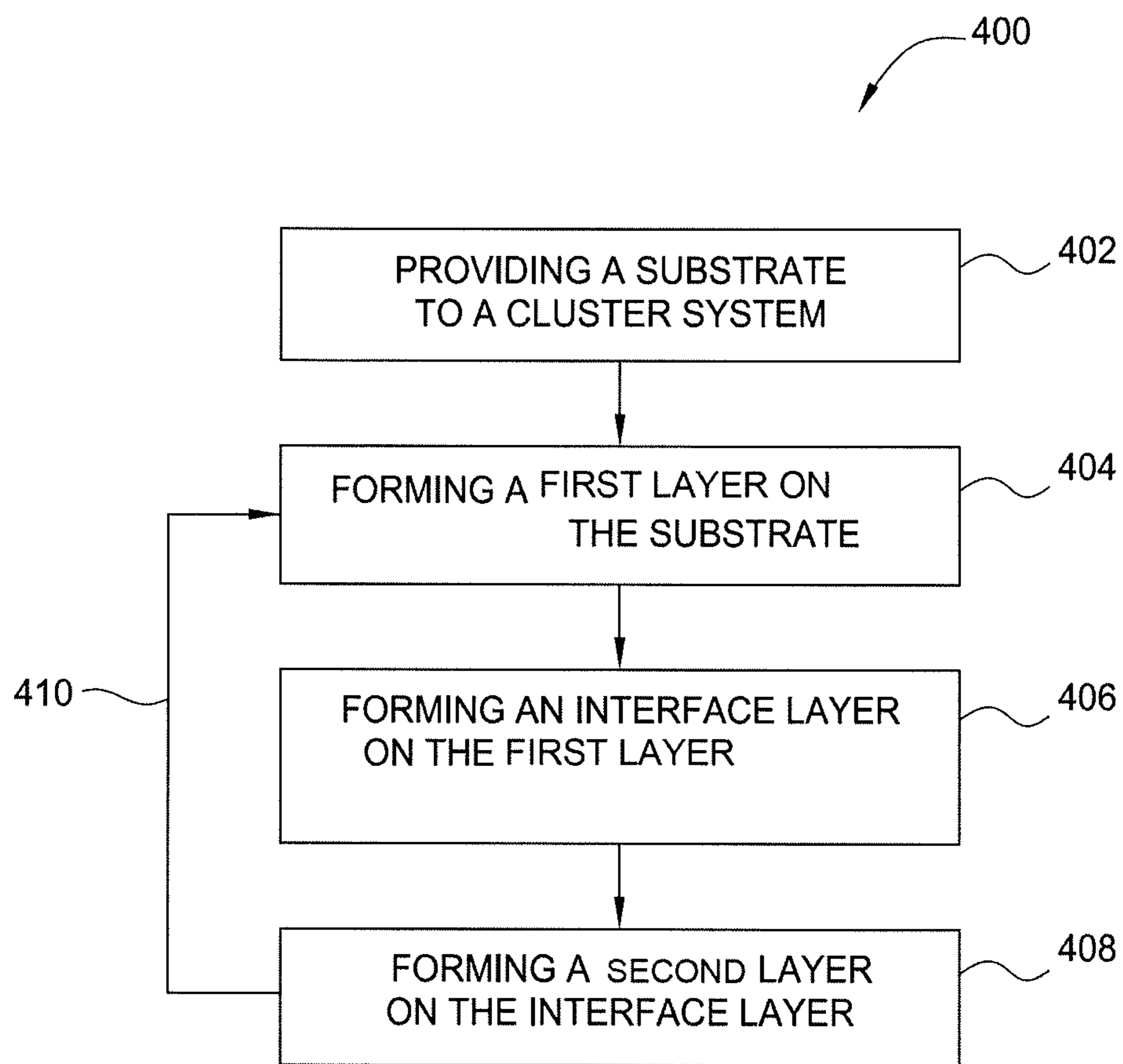


FIG. 4

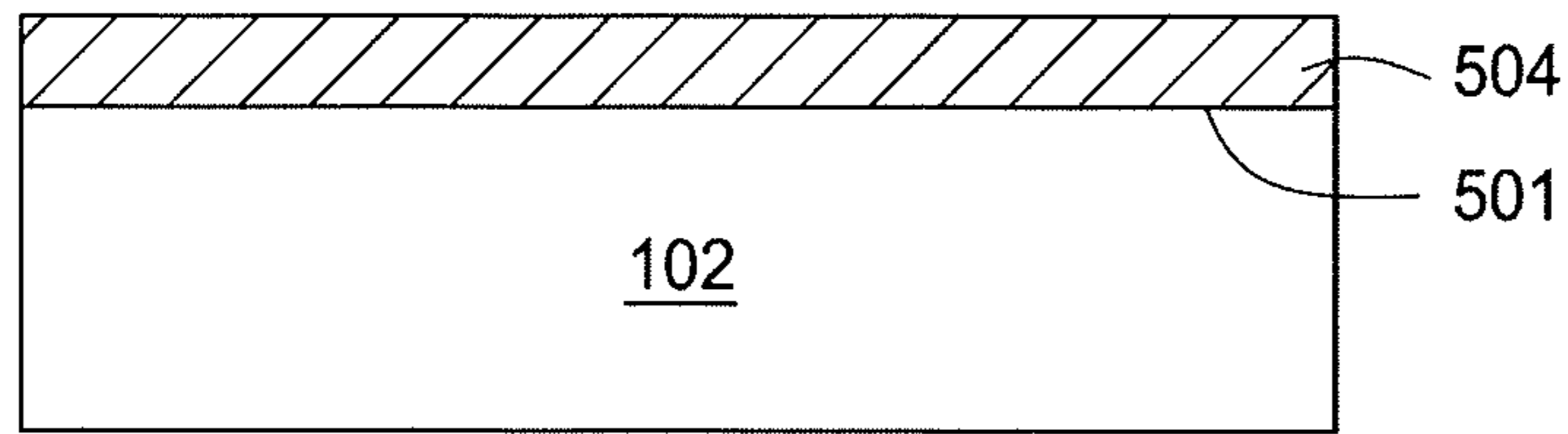


FIG. 5A

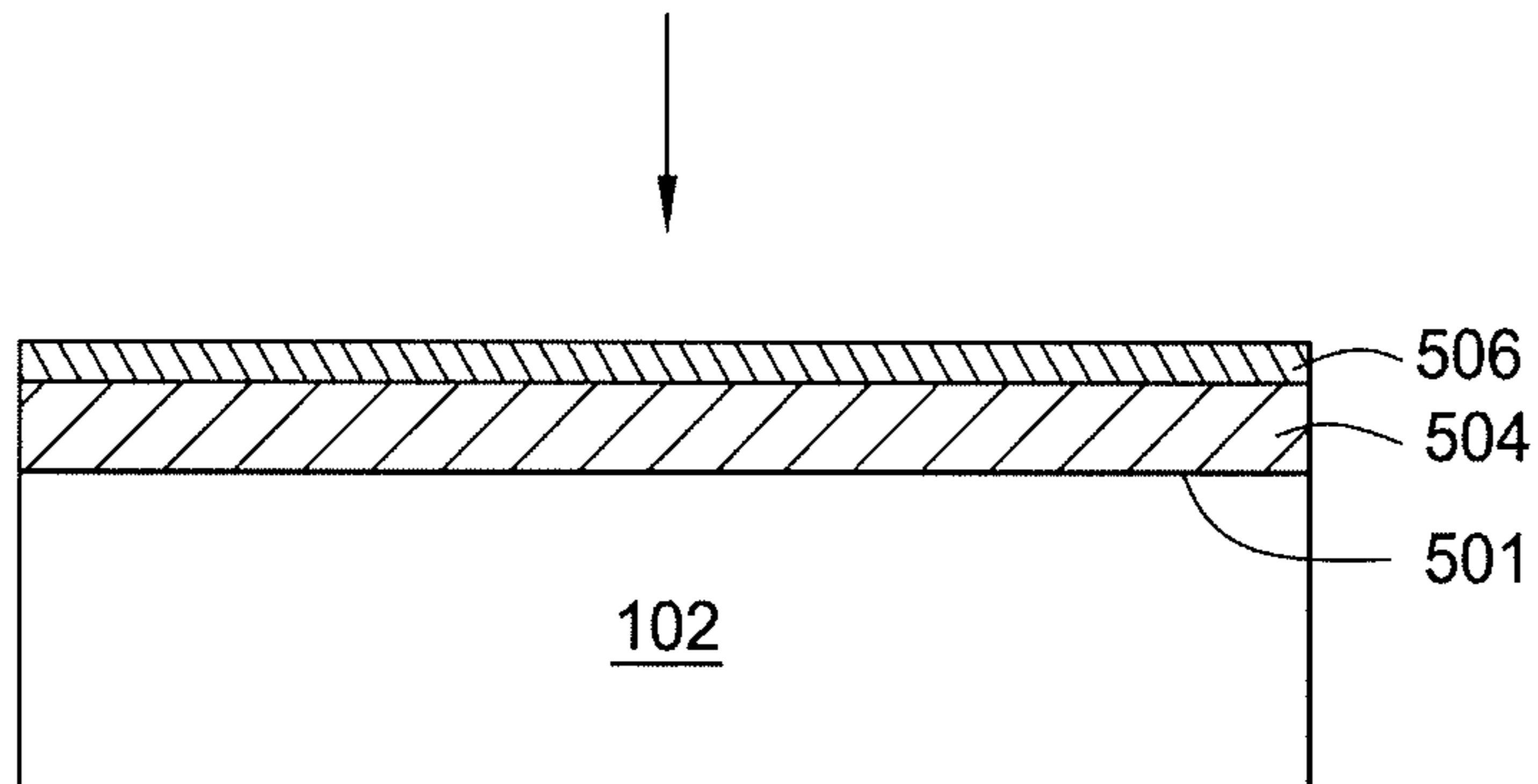


FIG. 5B

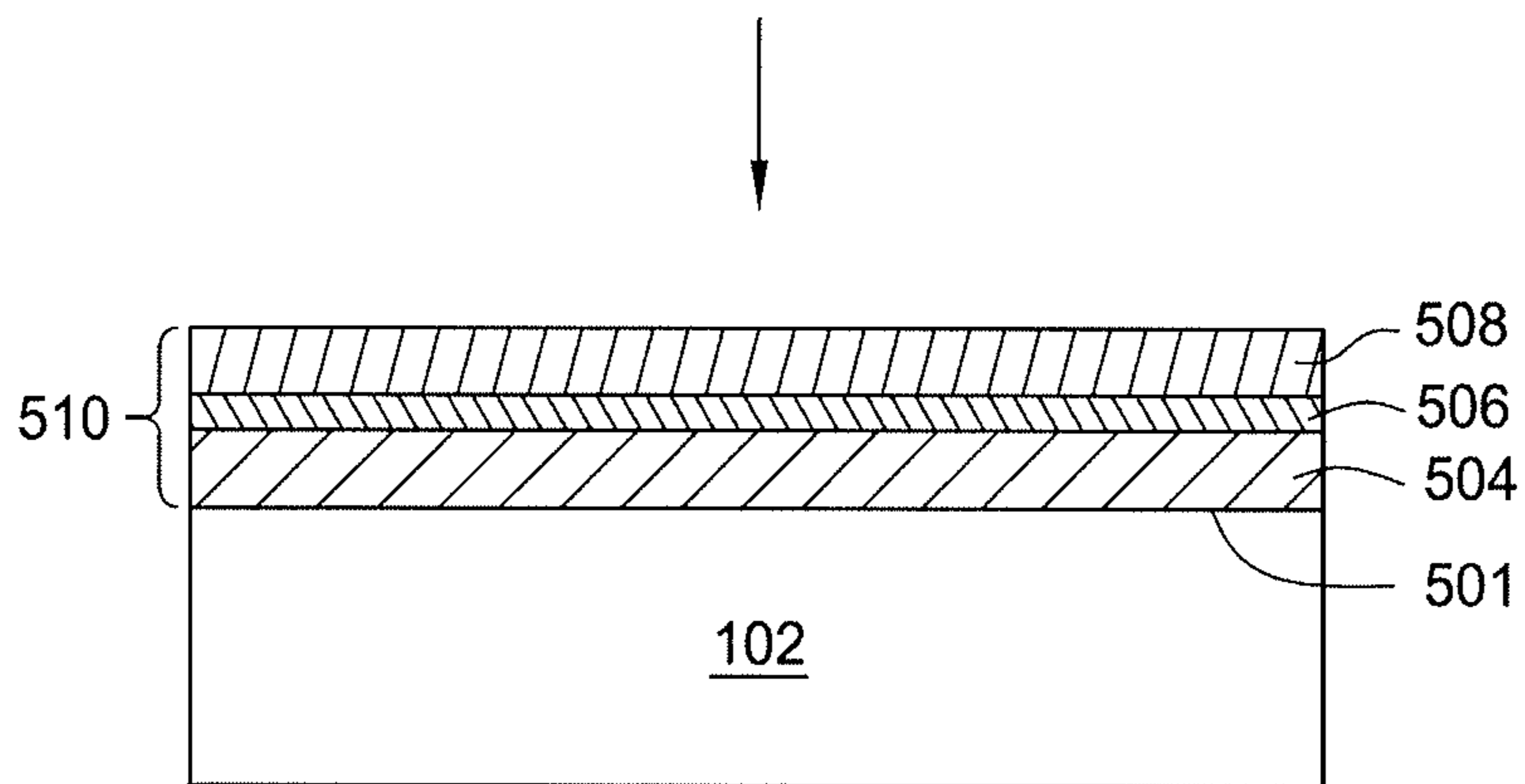


FIG. 5C

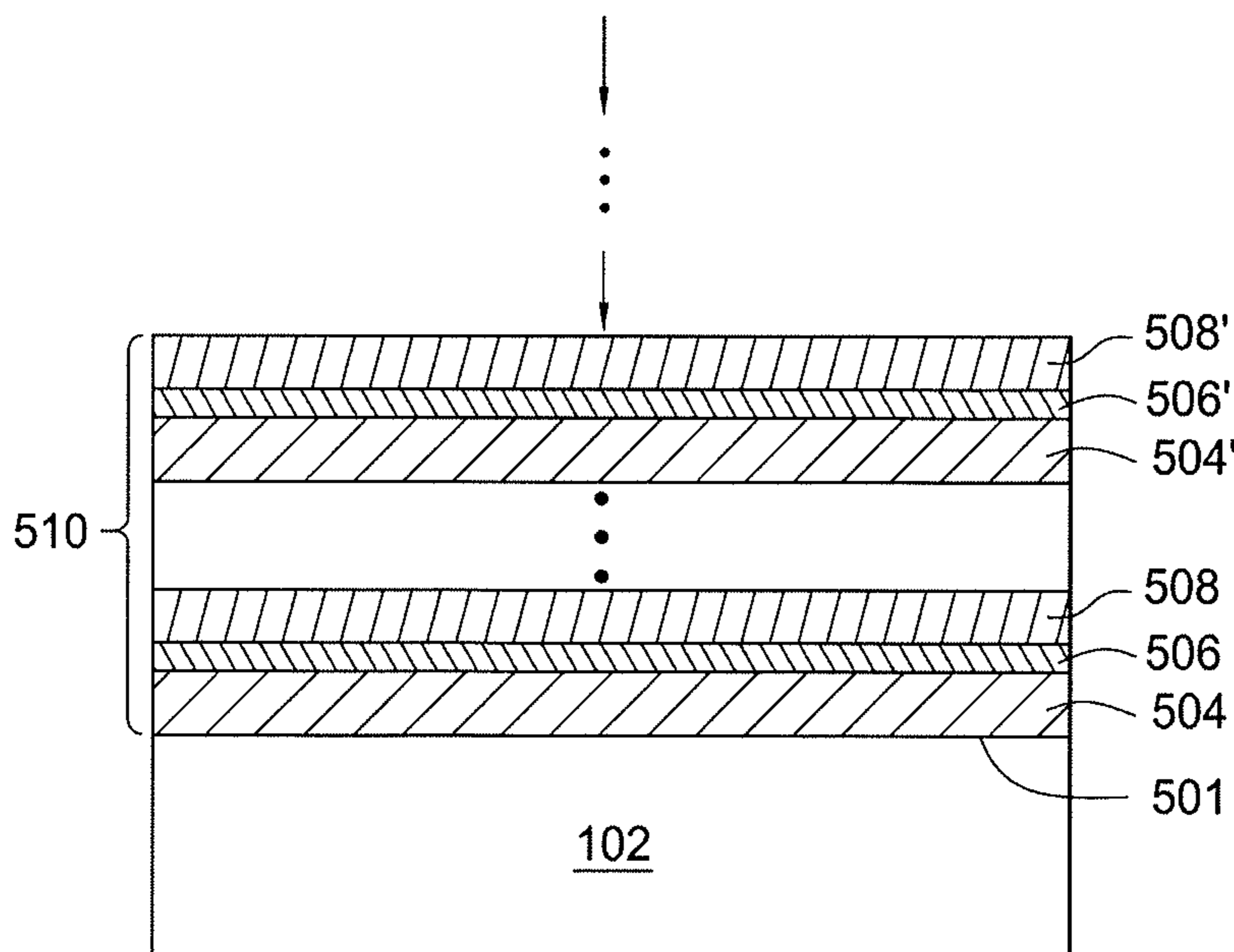


FIG. 5D

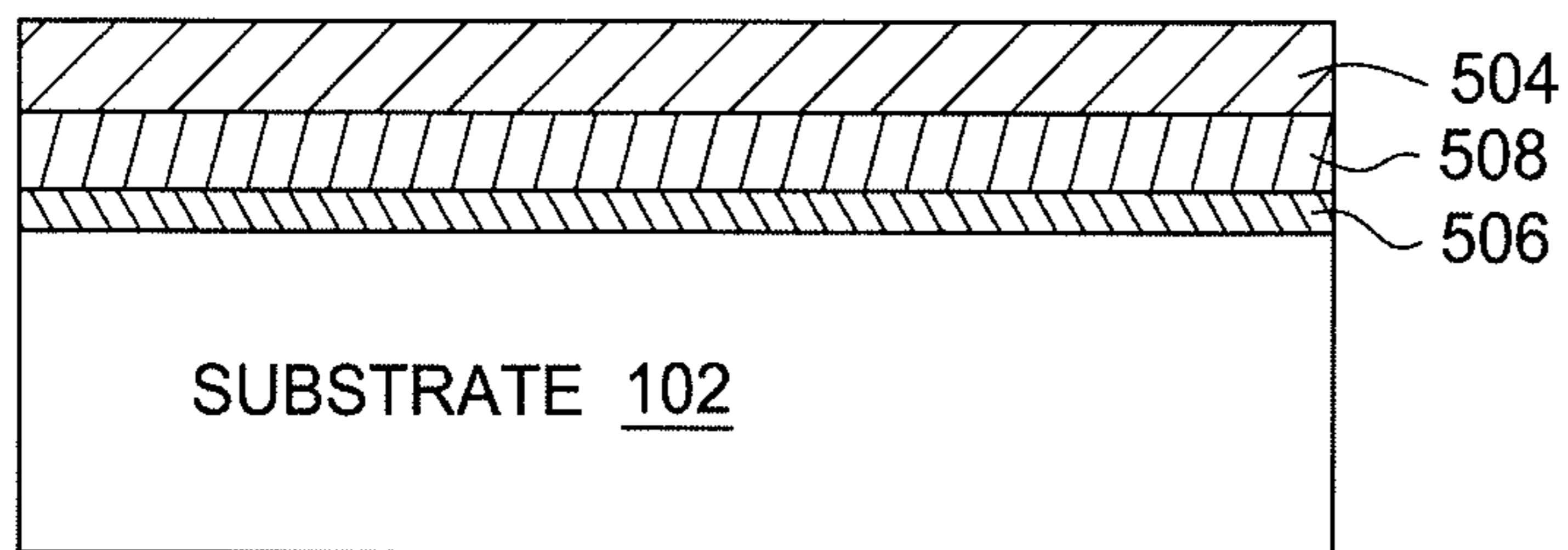


FIG. 5E



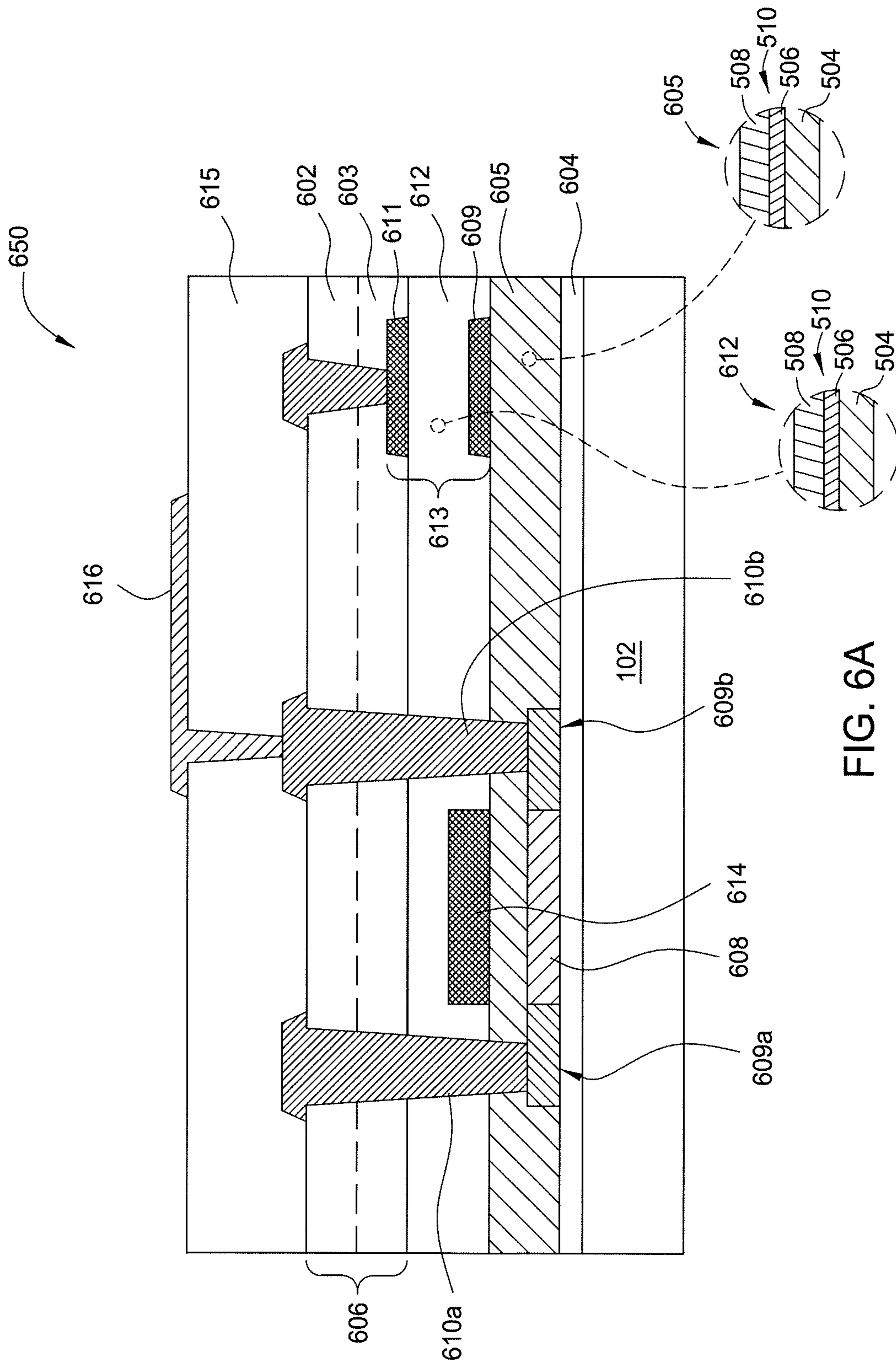


FIG. 6A

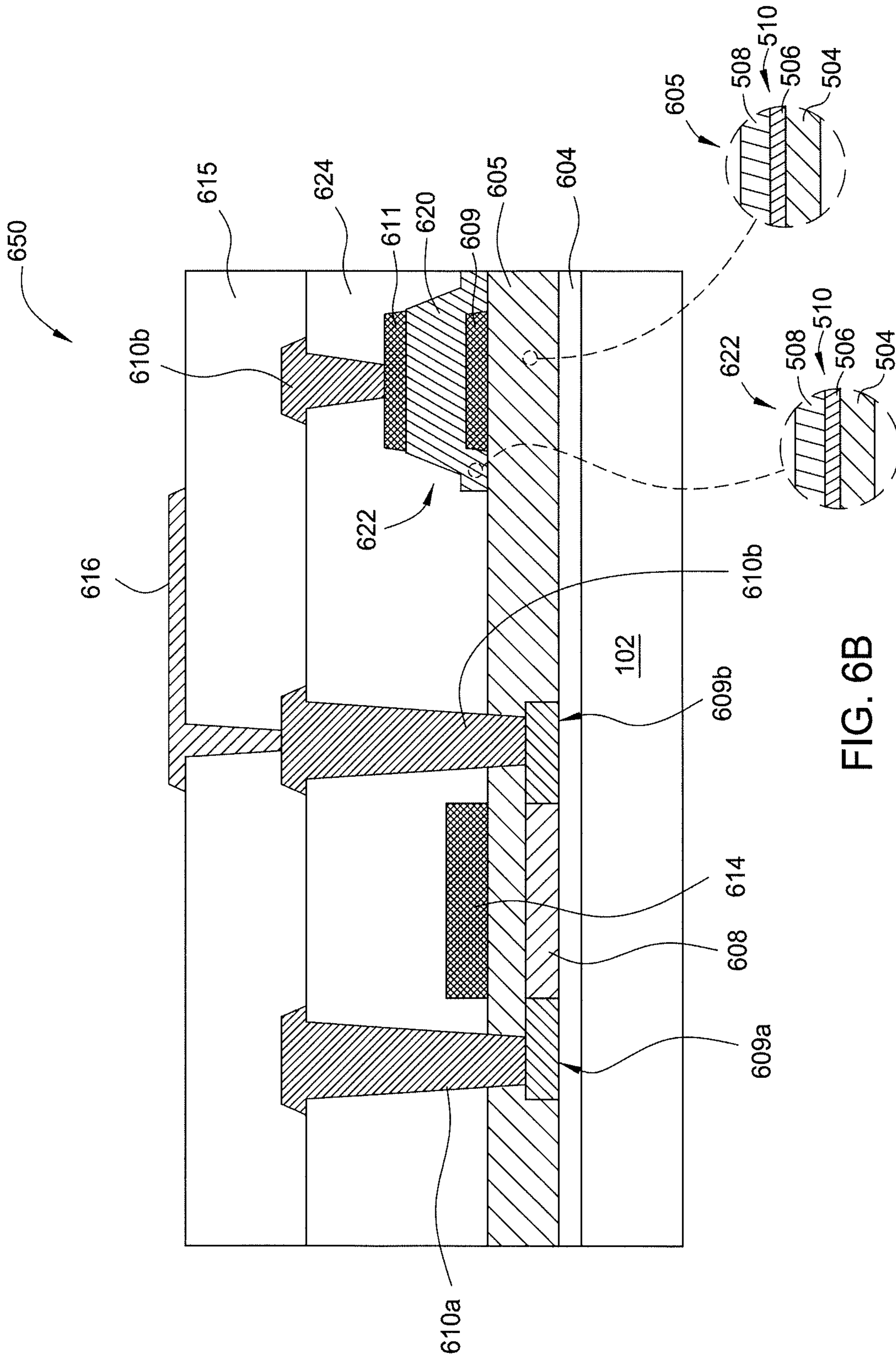


FIG. 6B

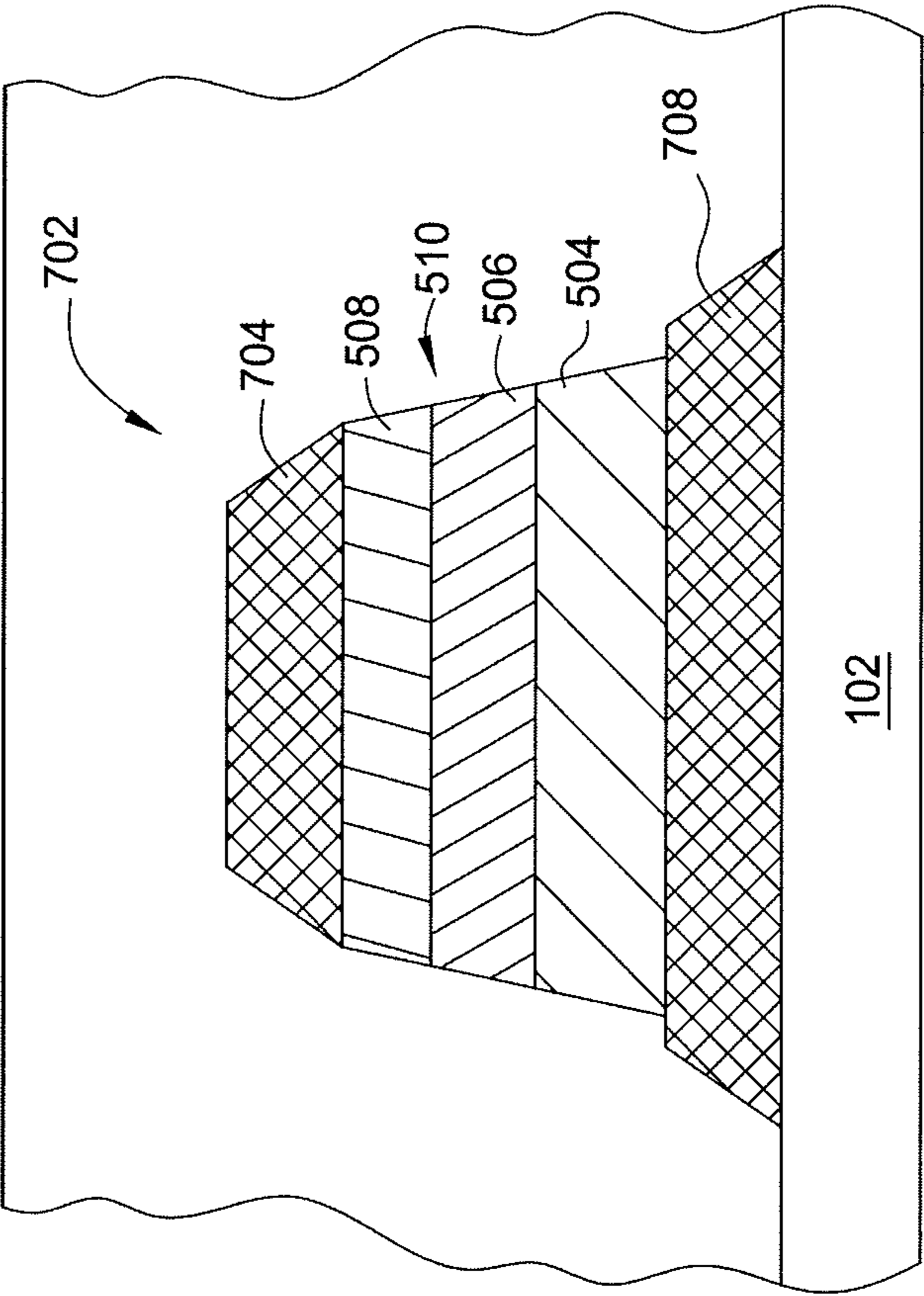


FIG. 7

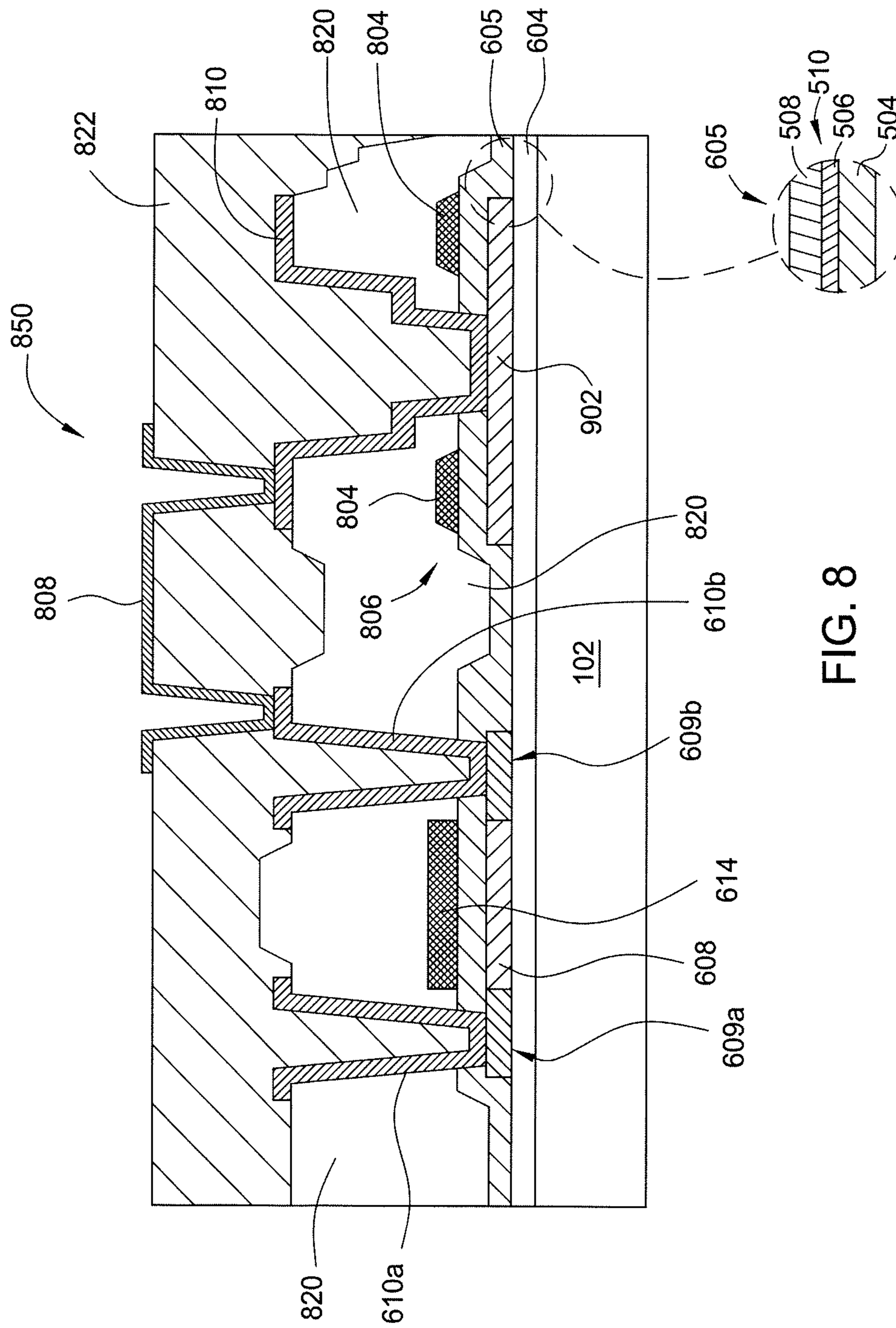


FIG. 8

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**HYBRID HIGH-K DIELECTRIC MATERIAL  
FILM STACKS COMPRISING ZIRCONIUM  
OXIDE UTILIZED IN DISPLAY DEVICES**

CROSS-REFERENCE TO RELATED  
APPLICATIONS

This application claims benefit of U.S. Provisional Application Ser. No. 62/364,140 filed Jul. 19, 2016, which is incorporated by reference in its entirety.

BACKGROUND

Field

Embodiments of the present disclosure generally relate to forming a hybrid film stack having a high dielectric constant for display devices. More particularly, embodiments of the disclosure relate to methods for forming a hybrid film stack having a film layer with a high dielectric constant fabricated by an atomic layer deposition (ALD) process with high film density and low film leakage for display applications.

Description of the Related Art

Display devices have been widely used for a wide range of electronic applications, such as TVs, monitors, mobile phone, MP3 players, e-book readers, personal digital assistants (PDAs) and the like. The display device is generally designed for producing a desired image by applying an electric field to a liquid crystal that fills a gap between two substrates (e.g., a pixel electrode and a common electrode) and has anisotropic dielectric constant that controls the intensity of the dielectric field. By adjusting the amount of light transmitted through the substrates, the light and image intensity, quality and power consumption may be efficiently controlled.

A variety of different display devices, such as active matrix liquid crystal display (AMLCD) or an active matrix organic light emitting diodes (AMOLED), may be employed as light sources for display. In the manufacturing of display devices, an electronic device with high electron mobility, low leakage current and high breakdown voltage, would allow more pixel area for light transmission and integration of circuitry, thereby resulting in a brighter display, higher overall electrical efficiency, faster response time and higher resolution displays. Low film qualities of the material layers, such as dielectric layers with impurities or low film densities, formed in the device often result in poor device electrical performance and short service life of the devices. Thus, a stable and reliable method for forming and integrating film layers within TFT and OLED devices becomes crucial to providing a device structure with low film leakage, and high breakdown voltage, for use in manufacturing electronic devices with lower threshold voltage shift and improved the overall performance of the electronic device.

In particular, the interface management between a metal electrode layer and the nearby insulating materials becomes critical as improper material selection of the interface between the metal electrode layer and the nearby insulating material may adversely result in undesired elements diffusing into the adjacent materials, which may eventually lead to current short, current leakage or device failure. Furthermore, the insulating materials with different, higher dielectric constants often provide different electrical performance, such as providing different capacitance in the device structures. Selection of the material of the insulating materials not

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only affects the electrical performance of the device, incompatibility of the material of the insulating materials to the electrodes may also result in film structure peeling, poor interface adhesion, or interface material diffusion, which may eventually lead to device failure and low product yield.

In some devices, capacitors, e.g., a dielectric layer placed between to electrodes, are often utilized and formed to store electric charges when the display devices are in operation. The capacitor as formed is required to have high capacitance for display devices. The capacitance may be adjusted by changing of the dielectric material and dimension of the dielectric layer formed between the electrodes and/or thickness of the dielectric layer. For example, when the dielectric layer is replaced with a material having a higher dielectric constant, the capacitance of the capacitor will increase as well. As the resolution requirement for display devices is increasingly challenging, e.g., display resolution greater than 800 ppi, only limited areas are remained in the display devices to allow forming capacitors therein to increase electrical performance. Thus, maintaining the capacitor formed in the display devices in a confined location with a relatively small area has become crucial.

Therefore, there is a need for improved methods for forming a dielectric layer with a high dielectric constant with desired film qualities and low leakage for manufacturing display devices that produce improved device electrical performance.

SUMMARY

Embodiments of the disclosure generally provide methods of forming a hybrid film stack that may be used as a capacitor layer or a gate insulating layer with a high dielectric constant as well as film qualities for display applications. In one embodiment, a thin film transistor structure includes gate, source and drain electrodes formed on a substrate, and an insulating layer formed on a substrate, wherein the insulating layer is a hybrid film stack having a dielectric layer comprising a zirconium containing material disposed on an interface layer formed above or below the gate, source and drain electrodes.

In another embodiment, a method for forming a hybrid film stack for display devices includes forming an interface layer of a hybrid film stack on a substrate, and forming a dielectric layer of the hybrid film stack by an ALD process on the interface layer, wherein the dielectric layer comprises zirconium containing material, wherein the hybrid film stack is utilized as a capacitor layer or an insulating layer in display devices.

In yet another embodiment, a device structure utilized for display devices includes a hybrid film stack using as a capacitor structure formed between two electrodes in display devices, wherein the hybrid film stack comprises an interface layer and a Zr containing layer formed on the interface layer.

BRIEF DESCRIPTION OF THE DRAWINGS

So that the manner in which the above recited features of the present disclosure are attained and can be understood in detail, a more particular description of the disclosure, briefly summarized above, may be had by reference to the embodiments thereof which are illustrated in the appended drawings.

FIG. 1 depicts a sectional view of a processing chamber that may be used to deposit a dielectric layer in accordance with one embodiment of the present disclosure;

FIG. 2 depicts a sectional view of a processing chamber that may be used to deposit a dielectric layer in accordance with one embodiment of the present disclosure;

FIG. 3 is a schematic view of a multi-chamber substrate processing system including processing chambers described herein

FIG. 4 depicts a process flow diagram of one embodiment of a method of forming a hydride film stack with high capacitance on a substrate;

FIG. 5A-5E are sectional views of one example of a hydride film stack with high capacitance of FIG. 4 formed therein;

FIGS. 6A-6B are cross sectional views of different examples of a display device structure with the hydride film stack with high capacitance of FIG. 4 formed therein;

FIG. 7 is a sectional view of a capacitor structure formed in a display device structure having a hydride film stack with high capacitance of FIG. 4 formed therein; and

FIG. 8 is a sectional view of one example of a display device structure having a hydride film stack with high capacitance of FIG. 4 formed therein.

To facilitate understanding, identical reference numerals have been used, where possible, to designate identical elements that are common to the figures. It is contemplated that elements and features of one embodiment may be beneficially incorporated in other embodiments without further recitation.

It is to be noted, however, that the appended drawings illustrate only exemplary embodiments of this disclosure and are therefore not to be considered limiting of its scope, for the disclosure may admit to other equally effective embodiments.

#### DETAILED DESCRIPTION

Embodiments of the disclosure generally provide methods of forming a hybrid film stack having a high dielectric constant greater than 9 with enhanced electrical performance, such as high capacitance and low leakage, with a high dielectric constant for display devices. Such dielectric layers with a high dielectric constant may be formed as a capacitor, a gate insulating layer, or any suitable insulating materials in display devices. The hybrid film stack having a high dielectric constant may be formed by a combination of chemical vapor deposition (e.g., PECVD or MOCVD) process and an atomic layer deposition (ALD) process (or a plasma enhanced ALD (PE-ALD)) that may provide a film stack with low defect density, low impurities, low film leakage and high dielectric constant. The hybrid film stack having a high dielectric constant may be utilized in any insulating structure and/or capacitor structures in TFT devices or OLED devices. In one example, the hybrid film stack with the high dielectric constant may be used in any suitable layers, such as a gate insulating layer, a capacitor layer formed between two electrodes, an inter-insulating layer, an etching stop layer or an interface protection layer in display devices for electric performance enhancement and improvement.

In some examples, the zirconium containing material as described in this disclosure may be exchanged or replaced with hafnium (Hf) containing material, including hafnium oxide, doped hafnium, doped hafnium oxide or the like.

FIG. 1 is a schematic cross-section view of one embodiment of a chemical vapor deposition processing chamber 100 in which a dielectric layer, such as an insulating layer, a capacitor layer formed between two electrodes, a gate insulating layer, an etch stop layer, a passivation layer, an

interlayer insulator, a dielectric layer for capacitors or passivation layer in display device structures, may be deposited. One suitable chemical vapor deposition chamber, such as plasma enhanced CVD (PECVD), is available from Applied Materials, Inc., located in Santa Clara, Calif. It is contemplated that other deposition chambers, including those from other manufacturers, may be utilized to practice the present disclosure.

The chamber 100 generally includes walls 142, a bottom 104 and a lid 112 which bound a process volume 106. A gas distribution plate 110 and substrate support assembly 130 are disposed within a process volume 106. The process volume 106 is accessed through a slit valve opening 108 formed through the wall 142 such that a substrate 102 may be transferred in to and out of the chamber 100.

The substrate support assembly 130 includes a substrate receiving surface 132 for supporting the substrate 102 thereon. A stem 134 couples the substrate support assembly 130 to a lift system 136 which raises and lowers the substrate support assembly 130 between substrate transfer and processing positions. A shadow frame 133 may be optionally placed over periphery of the substrate 102 when processing to prevent deposition on the edge of the substrate 102. Lift pins 138 are moveably disposed through the substrate support assembly 130 and are adapted to space the substrate 102 from the substrate receiving surface 132. The substrate support assembly 130 may also include heating and/or cooling elements 139 utilized to maintain the substrate support assembly 130 at a desired temperature. The substrate support assembly 130 may also include grounding straps 131 to provide an RF return path around the periphery of the substrate support assembly 130.

The gas distribution plate 110 is coupled at its periphery to a lid 112 or wall 142 of the chamber 100 by a suspension 114. The gas distribution plate 110 is also coupled to the lid 112 by one or more center supports 116 to help prevent sag and/or control the straightness/curvature of the gas distribution plate 110. It is contemplated that the one or more center supports 116 may not be utilized. The gas distribution plate 110 may have different configurations with different dimensions. In an exemplary embodiment, the gas distribution plate 110 has a quadrilateral plan shape. The gas distribution plate 110 has a downstream surface 150 having a plurality of apertures 111 formed therein facing an upper surface 118 of the substrate 102 disposed on the substrate support assembly 130. The apertures 111 may have different shapes, number, densities, dimensions, and distributions across the gas distribution plate 110. In one embodiment, a diameter of the apertures 111 may be selected between about 0.01 inch and about 1 inch.

A gas source 120 is coupled to the lid 112 to provide gas through the lid 112 and then through the apertures 111 formed in the gas distribution plate 110 to the process volume 106. A vacuum pump 109 is coupled to the chamber 100 to maintain the gas in the process volume 106 at a desired pressure.

An RF power source 122 is coupled to the lid 112 and/or to the gas distribution plate 110 to provide a RF power that creates an electric field between the gas distribution plate 110 and the substrate support assembly 130 so that a plasma may be generated from the gases present between the gas distribution plate 110 and the substrate support assembly 130. The RF power may be applied at various RF frequencies. For example, RF power may be applied at a frequency between about 0.3 MHz and about 200 MHz. In one embodiment the RF power is provided at a frequency of 13.56 MHz.

In one embodiment, the edges of the downstream surface **150** of the gas distribution plate **110** may be curved so that a spacing gradient is defined between the edge and corners of the gas distribution plate **110** and substrate receiving surface **132** and, consequently, between the gas distribution plate **110** and the upper surface **118** of the substrate **102**. The shape of the downstream surface **150** may be selected to meet specific process requirements. For example, the shape of the downstream surface **150** may be convex, planar, concave or other suitable shape. Therefore, the edge to corner spacing gradient may be utilized to tune the film property uniformity across the edge of the substrate, thereby correcting property non-uniformity in films disposed in the corner of the substrate. Additionally, the edge to center spacing may also be controlled so that the film property distribution uniformity may be controlled between the edge and center of the substrate. In one embodiment, a concave curved edge of the gas distribution plate **110** may be used so the center portion of the edge of the gas distribution plate **110** is spaced farther from the upper surface **118** of the substrate **102** than the corners of the gas distribution plate **110**. In another embodiment, a convex curved edge of the gas distribution plate **110** may be used so that the corners of the gas distribution plate **110** are spaced farther than the edges of the gas distribution plate **110** from the upper surface **118** of the substrate **102**.

A remote plasma source **124**, such as an inductively coupled remote plasma source, may also be coupled between the gas source and the gas distribution plate **110**. Between processing substrates, a cleaning gas may be energized in the remote plasma source **124** to remotely provide plasma utilized to clean chamber components. The cleaning gas entering the process volume **106** may be further excited by the RF power provided to the gas distribution plate **110** by the power source **122**. Suitable cleaning gases include, but are not limited to,  $\text{NF}_3$ ,  $\text{F}_2$ , and  $\text{SF}_6$ .

In one embodiment, the substrate **102** that may be processed in the chamber **100** may have a surface area of 10,000  $\text{cm}^2$  or more, such as 25,000  $\text{cm}^2$  or more, for example about 55,000  $\text{cm}^2$  or more. It is understood that after processing the substrate may be cut to form smaller other devices.

In one embodiment, the heating and/or cooling elements **139** may be set to provide a substrate support assembly temperature during deposition of about 600 degrees Celsius or less, for example between about 100 degrees Celsius and about 500 degrees Celsius, or between about 200 degrees Celsius and about 500 degrees Celsius, such as about 300 degrees Celsius and 500 degrees Celsius.

The nominal spacing during deposition between the upper surface **118** of the substrate **102** disposed on the substrate receiving surface **132** and the gas distribution plate **110** may generally vary between 400 mil and about 1,200 mil, such as between 400 mil and about 800 mil, or other distance required to obtain desired deposition results. In one exemplary embodiment wherein the gas distribution plate **110** has a concave downstream surface, the spacing between the center portion of the edge of the gas distribution plate **110** and the substrate receiving surface **132** is between about 400 mils and about 1400 mils, and the spacing between the corners of the gas distribution plate **110** and the substrate receiving surface **132** is between about 300 mils and about 1200 mils.

FIG. 2 is a schematic cross sectional view of an ALD (atomic layer deposition) chamber **200** that may be used to perform a deposition described herein. The ALD deposition process may be utilized to form a dielectric layer, such as an insulating layer, a gate insulating layer, an etch stop layer, an

interlayer insulator, a dielectric layer for capacitor or passivation layer in display devices as described herein. The chamber **200** generally includes a chamber body **202**, a lid assembly **204**, a substrate support assembly **206**, and a process kit **250**. The lid assembly **204** is disposed on the chamber body **202**, and the substrate support assembly **206** is at least partially disposed within the chamber body **202**. The chamber body **202** includes a slit valve opening **208** formed in a sidewall thereof to provide access to the interior of the processing chamber **200**. In some embodiments, the chamber body **202** includes one or more apertures that are in fluid communication with a vacuum system (e.g., a vacuum pump). The apertures provide an egress for gases within the chamber **200**. The vacuum system is controlled by a process controller to maintain a pressure within the ALD chamber **200** suitable for ALD processes. The lid assembly **204** may include one or more differential pumps and purge assemblies **220**. The differential pump and purge assemblies **220** are mounted to the lid assembly **204** with bellows **222**. The bellows **222** allow the pump and purge assemblies **220** to move vertically with respect to the lid assembly **204** while still maintaining a seal against gas leaks. When the process kit **250** is raised into a processing position, a compliant first seal **286** and a compliant second seal **288** on the process kit **250** are brought into contact with the differential pump and purge assemblies **220**. The differential pump and purge assemblies **220** are connected with a vacuum system (not shown) and maintained at a low pressure.

As shown in FIG. 2, the lid assembly **204** includes a RF cathode **210** that can generate a plasma of reactive species within the chamber **200** and/or within the process kit **250**. The RF cathode **210** may be heated by electric heating elements (not shown), for example, and cooled by circulation of cooling fluids, for example. Any power source capable of activating the gases into reactive species and maintaining the plasma of reactive species may be used. For example, RF or microwave (MW) based power discharge techniques may be used. The activation may also be generated by a thermally based technique, a gas breakdown technique, a high intensity light source (e.g., UV energy), or exposure to an x-ray source.

The substrate support assembly **206** can be at least partially disposed within the chamber body **202**. The substrate support assembly **206** can include a substrate support member or susceptor **230** to support a substrate **102** for processing within the chamber body. The susceptor **230** may be coupled to a substrate lift mechanism (not shown) through a shaft **224** or shafts **224** which extend through one or more openings **226** formed in a bottom surface of the chamber body **202**. The substrate lift mechanism can be flexibly sealed to the chamber body **202** by a bellows **228** that prevents vacuum leakage from around the shafts **224**. The substrate lift mechanism allows the susceptor **230** to be moved vertically within the ALD chamber **200** between a lower robot entry position, as shown, and processing, process kit transfer, and substrate transfer positions. In some embodiments, the substrate lift mechanism moves between fewer positions than those described.

In some embodiments, the substrate **102** may be secured to the susceptor using a vacuum chuck (not shown), an electrostatic chuck (not shown), or a mechanical clamp (not shown). The temperature of the susceptor **230** may be controlled (by, e.g., a process controller) during processing in the ALD chamber **200** to influence temperature of the substrate **102** and the process kit **250** to improve performance of the ALD processing. The susceptor **230** may be heated by, for example, electric heating elements (not

shown) within the susceptor **230**. The temperature of the susceptor **230** may be determined by pyrometers (not shown) in the chamber **200**, for example.

As shown in FIG. 2, the susceptor **230** can include one or more bores **234** through the susceptor **230** to accommodate one or more lift pins **236**. Each lift pin **236** is mounted so that the lift pin **236** may slide freely within a bore **234**. The support assembly **206** is movable such that the upper surface of the lift pins **236** can be located above the substrate support surface **238** of the susceptor **230** when the support assembly **206** is in a lower position. Conversely, the upper surface of the lift pins **236** is located below the upper substrate support surface **238** of the susceptor **230** when the support assembly **206** is in a raised position. When contacting the chamber body **202**, the lift pins **236** push against a lower surface of the substrate **102**, lifting the substrate off the susceptor **230**. Conversely, the susceptor **230** may raise the substrate **102** off of the lift pins **236**.

In some embodiments, the susceptor **230** includes process kit insulation buttons **237** that may include one or more compliant seals **239**. The process kit insulation buttons **237** may be used to carry the process kit **250** on the susceptor **230**. The one or more compliant seals **239** in the process kit insulation buttons **237** are compressed when the susceptor lifts the process kit **250** into the processing position.

FIG. 3 is a top plan view of a multi-chamber substrate processing system **300** suitable for the fabrication of any suitable display devices, such as organic light emitting diodes (OLEDs), thin-film transistors (TFT), thin-film encapsulation (TFE), and solar cell fabrication on flat media. The system **300** includes a plurality of processing chambers **100**, **200**, **340** and one or more load lock chambers **305**, **307** positioned around a central transfer chamber **315**. The processing chambers **100**, **200**, **340** may be configured to complete a number of different processing steps to achieve a desired processing of flat media, such as a large area substrate **102** (outlined in dashed lines). The load lock chambers **305**, **307** are configured to transfer a substrate in a quadrilateral form from an ambient environment outside the multi-chamber substrate processing system **300** to a vacuum environment inside the transfer chamber **315**.

Positioned within the transfer chamber **315** is a transfer robot **325** having an end effector **330**. The end effector **330** is configured to be supported and move independently of the transfer robot **325** to transfer the substrate **102**. The end effector **330** includes a wrist **335** and a plurality of fingers **342** adapted to support the substrate **102**. In one embodiment, the transfer robot **325** is configured to be rotated about a vertical axis and/or linearly driven in a vertical direction (Z direction) while the end effector **330** is configured to move linearly in a horizontal direction (X and/or Y direction) independent of and relative to the transfer robot **325**. For example, the transfer robot **325** raises and lowers the end effector **330** (Z direction) to various elevations within the transfer chamber **315** to align the end effector **330** with openings in the processing chambers **100**, **200**, **340** and the load lock chambers **305**, **307**. When the transfer robot **325** is at a suitable elevation, the end effector **330** is extended horizontally (X or Y direction) to transfer and/or position the substrate **102** into and out of any one of the processing chambers **100**, **200**, **340** and the load lock chambers **305**, **307**. Additionally, the transfer robot **325** may be rotated to align the end effector **330** with other processing chambers **100**, **200**, **340** and the load lock chambers **305**, **307**.

In one example, the processing chambers **100**, **200**, **340** incorporated in the multi-chamber substrate processing system **300** may be the chemical vapor deposition (PECVD or

MOCVD) chamber **100** depicted in FIG. 1 and the atomic layer deposition (ALD) (or a plasma enhanced ALD (PE-ALD) chamber) chamber **200** depicted in FIG. 2 and/or other suitable chambers, such as HDP-CVD, MOCVD, PECVD, ALD, PE-ALD thermal CVD, thermal annealing, PVD, surface treatment, electron beam (e-beam) treatment, plasma treatment, etching chambers, ion implantation chambers, surface cleaning chamber, metrology chambers, spin-coating chamber, polymer spinning deposition chamber, shadow frame storage chamber or any suitable chambers as needed. In one example depicted in the multi-chamber substrate processing system **300**, the system **300** includes the chemical vapor deposition (such as a PECVD) chamber **100**, the atomic layer deposition (ALD) chamber **200** (or a plasma enhanced ALD (PE-ALD) chamber) and other suitable chambers **340** as needed. By such arrangement, the dielectric layer formed by the ALD process and/or the PECVD process may also be integrated to perform in a single chamber without breaking vacuum so as to maintain cleanliness of the substrate without undesired contamination and residuals from the environment.

A portion of the interior of load lock chamber **305** has been removed to expose a substrate support or susceptor **350** that is adapted to receive and support the large area substrate **102** during processing. The susceptor **350** includes a plurality of lift pins **355** that are movable relative to an upper surface of the susceptor **350** to facilitate transfer of the large area substrate **102**. In one example of a transfer process of the large area substrate **102**, the lift pins **355** are extended away from or above the upper surface of the susceptor **350**. The end effector **330** extends in the X direction into the processing chamber **100**, **200**, **340** or load lock chambers **305**, **307** above the extended lift pins. The transfer robot **325** lowers the end effector **330** in the Z direction until the large area substrate **102** is supported by the lift pins **355**. The lift pins **355** are spaced to allow the fingers **342** of the end effector **330** to pass the lift pins **355** without interference. The end effector **330** may be further lowered to assure clearance between the large area substrate **102** and the fingers **342** and the end effector **330** is retracted in the X direction into the transfer chamber **315**. The lift pins **355** may be retracted to a position that is substantially flush with the upper surface of the susceptor **350** in order to bring the large area substrate **102** into contact with the susceptor **350** so the susceptor **350** supports the large area substrate **102**. A slit valve or door **360** between the transfer chamber **315** and the load lock chamber **305**, **307** (or the processing chamber or **100**, **200**, **340**) may be sealed and processing may be commenced in the load lock chamber **305**, **307** (or the processing chambers **100**, **200**, **340**). To remove the large area substrate **102** after processing, the transfer process may be reversed, wherein the lift pins **355** raise the large area substrate **102** and the end effector **330** may retrieve the large area substrate **102**. In one example, the substrate **102** may be transferred into the multi-chamber substrate processing system **300** through the first load lock chamber **305**. After the substrate **102** is oriented and aligned to a desired position, the substrate **102** is then transferred to any one of the processing chambers **100**, **200**, **340** through the transfer chamber **315** to perform any suitable processes as needed to form a device structure on the substrate **102**. After the processes are completed in the processing chambers **100**, **200**, **340**, then the substrate **102** is removed from and transferred out of the multi-chamber substrate processing system **300** from the second load lock chamber **307** as needed.



The environment in the substrate processing system **300** is isolated from ambient pressure (i.e. pressure outside the system **300**) and is maintained at a negative pressure by one or more vacuum pumps (not shown). During processing, the processing chambers **100**, **200**, **340** are pumped down to pre-determined pressures configured to facilitate thin film deposition and other processes. Likewise, the transfer chamber **315** is held at a reduced pressure during transfer of the large area substrates to facilitate a minimal pressure gradient between the processing chambers **100**, **200**, **340** and the transfer chamber **315**. In one embodiment, the pressure in the transfer chamber **315** is maintained at a pressure lower than ambient pressure. For example, the pressure in the transfer chamber may be about 7 Torr to about 10 Torr while the pressure in the processing chambers **100**, **200**, **340** may be lower. In one embodiment, the maintained pressure within the transfer chamber **315** may be substantially equal to the pressure within the processing chambers **100**, **200**, **340** and/or load lock chambers **305** and **307** to facilitate a substantially equalized pressure in the system **300**.

During the transfer of the large area substrate **102** in the transfer chamber **315** and the processing chambers **100**, **200**, **340**, proper alignment of the large area substrate **102** is crucial to prevent collisions and/or damage of the large area substrate **102**. Additionally, the interior of the system **300** must be kept clean and free from debris such as broken pieces of a substrate, broken equipment, and other particulate contamination. While some conventional systems include view windows allowing line of sight viewing into the interior of the various chambers **100**, **200**, **340**, the windows may not allow a full view and/or precise inspection of the large area substrates and the interior of the various chambers **100**, **200**, **340**. Also, the conventional systems are not configured to view the large area substrate **102** and provide a metric of processing results while the large area substrates are in the system.

The transfer robot **325** includes one or more optical image sensors **365** and **370** disposed on the transfer robot **325** as needed. The one or more optical image sensors **365**, **370** may be optical scanners, imagers or cameras, such as a charged-coupled device (CCD), a complementary metal oxide semiconductor (CMOS) device, a video camera, and the like. In one embodiment, one or more of the optical image sensors **365**, **370** are mounted on the transfer robot **325** in a position to view the large area substrate **102**, the fingers **342** and any object in the line of sight view of the sensors **365**, **370**. In this embodiment, the image sensors **365**, **370** may be oriented to view objects substantially in the X and Y direction as well as the Z direction as the transfer robot **325** is stationary or moving in the system **300**. The image sensors **365**, **370** may include wide angle optics, such as a fisheye lens, to enable a greater field of view.

FIG. 4 depicts a flow diagram of one embodiment of a process **400** for forming a hybrid film stack suitable for use in display devices, such as thin-film transistor devices or OLED devices. Such hybrid film stack may be formed as a capacitor layer disposed between two metal layers to form a capacitor, or an insulating layer in display devices. Suitable examples of the insulating layer used in display devices include a gate insulating layer, a capacitor layer disposed between two metal layers, an interface layer, a dielectric layer utilized to form a capacitor, an etch stop layer or a passivation layer where an insulating material is needed. The insulating layer may be formed by a plasma enhanced chemical vapor deposition (PECVD) process, which may be practiced in the processing chamber **100**, as described in FIG. 1, and/or an atomic layer deposition (ALD) process (or

a PEALD process), which may be practiced in the processing chamber **200**, as described in FIG. 2, or other suitable processing chamber, or in combination thereof.

The process **400** begins at operation **402** by providing the substrate **102** in a processing chamber, such as the processing chamber **100** (a PECVD chamber) or processing chamber **200** (an ALD chamber or a PEALD chamber) depicted in FIG. 2, to form an insulating layer or a dielectric layer. The substrate **102** may have different combinations of films, structures or layers previously formed thereon to facilitate forming different device structures or different film stacks on the substrate **102**. The substrate **102** may be any one of glass substrate, plastic substrate, polymer substrate, metal substrate, singled substrate, roll-to-roll substrate, or other suitable transparent substrate suitable for forming a thin film transistor thereon.

At operation **404**, a deposition process is then performed on the substrate **102** to form a first layer **504** of a hybrid film stack **510** (depicted in FIG. 5C) on the substrate **102**. In one example, the resultant hybrid film stack **510** may be formed as a gate insulating layer or a capacitor layer in display devices. In such example, the resultant hybrid film stack **510** of the gate insulating layer and/or the capacitor layer in display devices may be in form of multiple layers, which will be described later with reference to FIGS. 5B and 5C.

The first layer **504** is formed on a surface **501** of the substrate **102** by a plasma enhanced chemical vapor deposition (PECVD) process. The first layer **504** is a dielectric layer, such as a silicon containing layer. Suitable examples of the silicon containing layer may include silicon oxide, silicon oxynitride, silicon carbide, silicon oxycarbide or silicon nitride, formed by the CVD process. As silicon materials are widely used in display devices, the first layer **504** referred here could be any existing materials come with the substrate pre-formed in the display devices prior to a second layer **508** (depicted in FIG. 5B) to be formed thereon. In one example, the first layer **504** is a silicon nitride or a silicon oxide material.

In one example wherein the substrate **102** already includes a silicon containing material pre-fabricated thereon, the first layer **504** may be eliminated and the process **400** for forming the hybrid film stack **510** may be directly start from operation **406** to form the interface layer **506**.

At operation **406**, an interface layer **506** is formed on the first layer **504**, as shown in FIG. 5B. As the second layer **508** (shown in FIG. 5C) formed thereon is a dielectric layer with high dielectric constant that includes certain metal elements, direct contact of the elements (e.g., metal elements or oxygen elements) from the second layer **508** with the silicon elements from the first layer **504** often result in interface diffusion, which may result in a undesired diffusion layer formed at the interface. The elements (e.g., metal elements or oxygen elements) from the second layer **508** diffused and penetrated into the first layer **504** forms a thin lower dielectric constant film (or other types of materials) at the interface deteriorating the film qualities of the overall hybrid film stack **510**, especially the degrade of the dielectric constant of the hybrid film stack **510**. Thus, by forming the interface layer **506** between the first layer **504** and the second layer **508**, the second layer **508** is then interfaced with the interface layer **506**, which is more inert to the film properties from both the first and the second layer **504**, **508**, rather than in direct contact with the first layer **504** so that good interface control may be obtained.

In the embodiments wherein the second layer **508** is manufactured from a material that does not create interface diffusion layer to the first layer **504**, the interface layer **506**

as described here may be eliminated. In such embodiments, the second layer **508** may be formed directly and in direct contact with the first layer **504**.

In one example, the interface layer **506** is metal dielectric layer formed by a plasma enhanced chemical deposition process, such as the processing chamber **100** depicted in FIG. **1**, or an atomic layer deposition processing chamber **200** (or a PE-ALD processing chamber) depicted in FIG. **2**. In one example, the interface layer **506** may be an aluminum containing material, such as aluminum oxide ( $\text{Al}_2\text{O}_3$ ), aluminum nitride (AlN) layer aluminum oxide ( $\text{Al}_2\text{O}_3$ ), aluminum nitride (AlN), aluminum titanium oxide (AlTiO), aluminum zirconium oxide (AlZrO), or AlON, or a yttrium oxide containing material, such as  $\text{Y}_2\text{O}_3$ . In one particular example, the interface layer **506** is an aluminum oxide ( $\text{Al}_2\text{O}_3$ ) or aluminum nitride (AlN) layer.

The ALD process is enabled by a slow deposition process with a first monolayer of atoms being absorbed and adhered on a second monolayer of atoms formed on a substrate surface. Strong adherence of atoms in each layers and absorbability of the layers of atoms onto the surface of substrate provide compact and secured bonding structures in the film structures so as to render a film property with a high film density (compared to a chemical vapor deposition process) that may efficiently prevent atoms or elements from penetrating therethrough. Furthermore, the slow ALD deposition rate of the interface layer **506** also allows the atoms from the interface layer **506** to gradually fill in the pinholes, pores, pits or defects that may be occurred from the substrate surface (e.g., the first layer **504** in the examples of FIG. **5B**) so as to assist repairing the film defects from the substrate surface. In contrast, the conventional plasma enhanced chemical vapor deposition process (PECVD) often provides a relatively fast deposition process with high throughput but renders relatively porous film structures for the resultant film layer. The interface layer **506** serves as a barrier/blocking layer to prevent elements from the first and the second layers **504**, **508** to penetrate or diffuse therethrough to undesirably alter the device performance. In the example wherein high throughput of the manufacturing cycles is desired, a plasma assisted atomic layer deposition (PE-ALD) process may be utilized instead to provide a relatively higher deposition rate (compared to thermal ALD) of deposition process while still maintaining the desired degree of film density. In some embodiment wherein even higher throughput of the manufacturing cycles is desired, the interface layer **506** may be configured to formed by a CVD process while the second layer **508**, a high dielectric constant greater than 15, subsequently formed thereon is then formed by an ALD process to ensure the particular film properties, e.g., high film dielectric constant and low leakage, is achieved for the overall hybrid film stack **510**.

In one example, the precursors used in the ALD process for forming the interface layer **506** as a  $\text{Al}_2\text{O}_3$  layer includes at least a metal containing precursor, such as an aluminum containing gas, and a reacting gas. Suitable examples of the aluminum containing gas may have a formula of  $\text{R}_x\text{Al}_y\text{R}'_z\text{R}''_v$ , or  $\text{R}_x\text{Al}_y(\text{OR}')_z$ , where R, R' and R'' are H,  $\text{CH}_3$ ,  $\text{C}_2\text{H}_5$ ,  $\text{C}_3\text{H}_7$ , CO, NCO, alkyl or aryl group and x, y, z and v are integers having a range between 1 and 8. In another embodiment, the aluminum containing compound may have a formula of  $\text{Al}(\text{NRR}')_3$ , where R and R' may be H,  $\text{CH}_3$ ,  $\text{C}_2\text{H}_5$ ,  $\text{O}_3\text{H}_7$ , CO, NCO, alkyl or aryl group and R' may be H,  $\text{CH}_3$ ,  $\text{C}_2\text{H}_5$ ,  $\text{C}_3\text{H}_7$ , CO, NCO, alkyl or aryl group. Examples of suitable aluminum containing compounds are diethylaluminum ethoxide ( $\text{Et}_2\text{AlOEt}$ ), triethyl-tri-sec-butoxy dialuminum ( $\text{Et}_3\text{Al}_2\text{OBu}_3$ , or EBDA), trimethylalumi-

num (TMA), trimethyldialuminum ethoxide, dimethyl aluminum isopropoxide, di-sec-butoxy aluminum ethoxide,  $(\text{OR})_2\text{AlR}'$ , wherein R, R' and R'' may be methyl, ethyl, propyl, isopropyl, butyl, isobutyl, tertiary butyl, and other alkyl groups having higher numbers of carbon atoms, and the like.

The reacting gas that may be supplied to form aluminum containing material gas includes an oxygen containing gas, such as, oxygen ( $\text{O}_2$ ), ozone ( $\text{O}_3$ ), nitrogen ( $\text{N}_2$ ),  $\text{N}_2\text{O}$ ,  $\text{CO}_2$ , NO, CO,  $\text{CO}_2$  and among others.

In one example, the interface layer may have a thickness of between about 1.5 Å and about 30 Å, such as about 10 Å.

At operation **408**, after the interface layer **506** is formed on the first layer **504**, the second layer **508** is then formed on the interface layer **506**. The second layer **508** is formed by the atomic layer deposition process comprising Zr containing material. In one example, the second layer **508** is a Zr containing material, such as zirconium oxide ( $\text{ZrO}_2$ ), formed in cubic or tetragonal structures, providing the second layer **508** with high dielectric constant greater than 25. A  $\text{ZrO}_2$  layer formed by an atomic layer deposition process often predominately provides the resultant  $\text{ZrO}_2$  in crystalline structure in cubic or tetragonal phase, providing a dielectric constant at least greater than 25, such as between about 25 and about 50. The Zr containing layer formed as the second layer **508** of the hybrid film stack **510** by an atomic layer deposition (ALD) process may provide good film properties, such as high film density, low defect density and the like as well as the desired high dielectric constant.

In one example, the precursor mixtures utilized to form the second layer **508** include alternatively or sequentially supplying a zirconium containing precursor with or without the reactive gaseous species to form an aluminum doped zirconium (Zr) containing layer. Suitable zirconium containing precursor include Zr-organometallic precursors, such as tetrakis(ethylmethylamino)zirconium (TEMAZ), tris(dimethylamino)cyclopentadienyl zirconium  $(\text{C}_5\text{H}_5)\text{Zr}[\text{N}(\text{CH}_3)_2]_3$ , or the like. In one particular example utilized herein, the zirconium containing precursor is tetrakis(ethylmethylamino)zirconium (TEMAZ). The reactive gaseous species may be oxygen containing gases, such as  $\text{H}_2\text{O}$ ,  $\text{O}_2$ ,  $\text{O}_3$ ,  $\text{H}_2\text{O}_2$ ,  $\text{CO}_2$ ,  $\text{NO}_2$ ,  $\text{N}_2\text{O}$ , and the like. In one example, the oxygen containing gas is  $\text{O}_2$  or  $\text{O}_3$ .

In one example, the second layer **508** of the hybrid film stack **510** as formed may have a dielectric constant greater than 25, such as between 25 and 50. In one example, the second layer **508** of the hybrid film stack **510** has a thickness between about 250 Å and about 900 Å.

In some examples, the Zr containing layer formed in the second layer **508** may have dopants doped therein to keep a current leakage at a desired low level. As the dielectric constant of a material increases, the band gap of the material decreases, leading to high leakage current in the device. Thus, higher dielectric constant, e.g., greater than 25, of a dielectric layer is desired for the advanced technologies so as to provide a capacitor with higher capacitance. In contrast, higher dielectric constant, e.g., greater than 25, of the dielectric layer also often results in high film leakage that may eventually lead to device failure. Thus, by providing dopants, such as the aluminum dopants, into the Zr containing layer in the second layer **508**, the crystalline structure of the Zr containing layer in the second layer **508** may be altered into an amorphous state, thus lowering the dielectric constant of a certain predetermined level so as to keep the current leakage at a desired low level. For example, by providing aluminum dopant into the  $\text{ZrO}_2$  structure to form the second layer **508** may render the resultant  $\text{ZrO}_2$  structure in amorphous state, thus, keeping the dielectric constant of

the amorphous aluminum doped ZrO<sub>2</sub> at a desired range less than 25 but still above 15, such as between about 15 and 25. Alternatively, the second layer **508** may be formed including both amorphous and crystalline structures, such as a portion of the ZrO<sub>2</sub> layer with dopants and another portion without dopants (e.g., a hybrid bonding structure), so as to obtain the resultant hydride film stack **510** with desired dielectric constant level, as well as desired low leakage level and good interface control.

In the example wherein the doped ZrO<sub>2</sub> layer is used for the second layer **508**, the doped ZrO<sub>2</sub> layer dielectric constant greater than 15, such as between 15 and 25 and a film leakage about 1E-8 A/cm<sup>2</sup> or below. The aluminum dopant in a ZrO<sub>2</sub> structure may have a doping concentration between about 6 atm. % and about 20 atm. %.

It is noted that the first layer **504**, the interface layer **506** and the second layer **508** of the hybrid film stack **510** may be all formed in the same processing system, such as the processing system **300** depicted in FIG. 3 without breaking vacuum. For example, the first layer **504** may be formed in the processing **100** integrated in the processing system **300**. The interface layer **506** may be formed in the processing chamber **100** or processing chamber **200** integrated in the processing system **300** while the second layer **508** may be formed in the processing chamber **200** all integrated in the processing system **300** as needed to save manufacturing cycling time as well as maintaining low substrate contaminant as needed.

It is noted that the operation **404**, **406**, **408** may be performed as many times as needed, as indicated by the loop **410**, to cyclically form the first layer **504**, the interface layer **506** and the second layer **508**, until a desired number of the first layer **504**, interface layer **506** and the second layer **508** are formed for the hybrid film stack **510**. The process parameters in each operation may be changed when cyclically these operations to fine tune the film properties formed on the substrate. In the example depicted in FIG. 5D, an upper most first layer **504'** and an upper most interface layer **506'** and an upper most second layer **508'** are formed to reach a desired thickness of the overall hybrid film stack **510**.

By forming the multiple layers for the hybrid film stack **510** as shown in FIG. 5D, the substrate **102** is transferred between the processing chamber (PECVD chamber) **100** and the processing chamber **200** (ALD chamber) as many times as needed to reach the desired thickness or the desired numbers of the first layer **504**, interface layer **506** and the second layer **508** for the hybrid film stack **510**. As discussed above, the processing chamber (PECVD chamber) **100** and the processing chamber **200** (ALD chamber) may be integrated in a single processing system, such as the processing system **300** in FIG. 3, the substrate **102** may be transferred in and out between the processing chamber (PECVD chamber) **100** and the processing chamber **200** (ALD chamber) in the processing system **300** without breaking vacuum so as to maintain the production efficiency and manufacturing throughput.

In some embodiments, the hybrid film stack **510** may start with the interface layer **506** and the second layer **508** formed on the substrate **102** followed by the first layer **504** formed on the second layer **508**, as shown in FIG. 5E. Similarly, the interface layer **506**, the second layer **508** and the first layer **504** may be formed multiple times (e.g., continuously cycling the substrate **102** between the ALD processing chamber **200** and the PECVD processing chamber **100**) to form the interface layer **506**, second layer **508** and the first layer **504** sequentially. In the embodiment where the interface layer **506** is not present, the second layer **508** may be

directly formed on and in direct contact with the substrate **102** and the first layer formed on the substrate.

It is noted that the cycles of the depositions among operation **404**, **406**, **408**, as indicated by the loop **410**, may be resumed or stopped in any operations as needed. The cycles of the depositions among operations **404**, **406**, **408**, as indicated by the loop **410**, may also skip some operations as needed. For example, as discussed above, in the embodiment wherein interface layer **506** is not required, the cycles of deposition may be performed between operation **404** and **408** and the last operation may be terminated or stopped at operation **404** or **408** as needed. Alternatively, after a first cycle of deposition of operation **404**, and/or **406** and/or **408** is completed, a second cycle of deposition may be started at any of the operation from operation **404**, **406** or **408** as needed to any of the first layer **504**, interface layer **506** and the second layer **508**.

Although the loop **410** indicates the operations may be continuously performed, it is noted that the operation **404**, **406**, **408** may be cycled for one or two times, generally, to prevent over-heating to the substrate **102** or low manufacturing throughput. For example, the operation **404**, **406**, **408** may be looped for one or two times to form the hybrid film stack **510** including two layers of the second layer **508** formed on the first layer **504** (the interface layer **506** not present) or vice versa, or three layers having the first layer **504** sandwiched between two second layers **508**, or three layers having the second layer **508** sandwiched between two first layers **504** (the interface layer **506** not present). The interface layer **506**, when present, may be added at any interface below, above and between the first and the second layers **504**, **508**.

FIG. 6A depicts an example of a TFT device structure **650** utilizing the hybrid film stack **510** in the TFT device structure **650** to form a capacitor, or a gate insulating layer, or other suitable insulating layers. A portion of the exemplary TFT device structure **650** is depicted in FIG. 6A formed on the substrate **102**. The TFT device structure **650** comprises a low temperature polysilicon (LTPS) TFT for OLED device. The LTPS TFT device structures **650** are MOS devices built with a source region **609a**, channel region **608**, and drain region **609b** formed on the optically transparent substrate **102** with or without an optional insulating layer **604** disposed thereon. The source region **609a**, channel region **608**, and drain region **609b** are generally formed from an initially deposited amorphous silicon (a-Si) layer that is typically later thermal or laser processed to form a polysilicon layer. The source, drain and channel regions **609a**, **608**, **609b** can be formed by patterning areas on the optically transparent substrate **102** and ion doping the deposited initial a-Si layer, which is then thermally or laser processed (e.g., an Excimer Laser Annealing process) to form the polysilicon layer. A gate insulating layer **605** (e.g., the insulating layer or the hybrid film stack **510** with high dielectric constant formed by the process **400** of FIG. 4) may be then deposited on top of the deposited polysilicon layer(s) to isolate a gate electrode **614** from the channel region **608**, source region **609a** and drain regions **609b**. The gate electrode **614** is formed on top of the gate insulating layer **605**. The gate insulating layer **605** is also commonly known as a gate oxide layer. A capacitor layer **612** (e.g., may also be the insulating layer or the hybrid film stack **510** formed by the process **400** of FIG. 4) and device connections are then made through the insulating material to allow control of the TFT device. As indicated by the circles in FIG. 6A, the gate insulating layer **605** and the capacitor layer **612** in the TFT device structure **650** may also be fabricated by the hybrid

film stack **510** with high dielectric constant as well as the low film leakage including the first layer **504** and the second layer **508** and the interface layer **506** formed therebetween. In the embodiment wherein the optional insulating layer **604** is present, the first layer **504** comprising the silicon containing layer may be eliminated as the optional insulating layer **604** and the first layer **504** may both be formed from a silicon material.

The TFT device structure **650** of FIG. **6A** is just partially formed for ease of description and explanation regarding to where the hybrid film stack **510** may be utilized in some locations in the device structure **650** utilized to form either the gate insulating layer **605** or the capacitor layer **612**, or both, in the device structure **650**.

After the capacitor layer **612** is formed, an interlayer insulator **606** may be formed on the capacitor layer **612**. The interlayer insulator **606** may be any suitable dielectric layer, such as silicon oxide or silicon nitride materials. The interlayer insulator **606** may be in form of a single layer formed on the capacitor layer **612**. Alternatively, the interlayer insulator **606** may be in form of multiple layers as needed for different device requirements. In the example depicted in FIG. **6A**, the interlayer insulator **606** includes a first dielectric layer **602** of silicon nitride formed on a second layer **603** of a silicon oxide layer. Subsequently, a source-drain metal electrode layer **610a**, **610b** is then deposited, formed and patterned in the interlayer insulator **606**, the capacitor layer **612** and the gate insulating layer **605** electrically connected to the source region **609a** and drain regions **609b**.

After the source-drain metal electrode layer **610a**, **610b** is patterned, the planarization layer **615** is then formed over the source-drain metal electrode layer **610a**, **610b**. The planarization layer **615** may be fabricated from polyimide, benzocyclobutene-series resin, spin on glass (SOG) or acrylate. The planarization layer **615** is later patterned to allow a pixel electrode **616** to be formed on and filled in the planarization layer **615**, electrically connecting to the source-drain metal electrode layer **610a**, **610b**.

In this example depicted in FIG. **5A**, the capacitor layer **612** is formed on the gate electrode **614** extending to a capacitor structure **613** (e.g., a MIM (metal-insulating-metal) structure) formed between an upper electrode **611** and a lower electrode **609**. The upper electrode **611** may be laterally coupled to the source-drain metal electrode layer **610a**, **610b** while the lower electrode **609** may be laterally coupled to the gate electrode **614**, or other suitable electrodes in the device structure **650**. The capacitor structure **613** formed in the device structure **650** may be a storage capacitor that may improve the display device electrical performance. It is noted that the capacitor structure **613** may be formed in any location suitable in the device structure **650** as needed for different device performance requirements.

In another example depicted in FIG. **6B**, a capacitor structure **622**, similar to the capacitor structure **613** depicted in FIG. **6A**, may be formed with different dimensions and/or profiles of the hybrid film stack **510** severing as a capacitor layer **620** formed between the upper electrode **611** and the lower electrode **609**. Unlike the capacitor layer **612** shown in FIG. **6A** that extends from the area above the gate electrode **614** to the area between the upper and the lower electrode **611**, **609**, the capacitor layer **620** depicted in FIG. **6B** is formed substantially in the area between the upper and the lower electrodes **611**, **609**. Thus, a regular interlayer insulator **624** comprising silicon oxide or silicon oxide may be formed on the gate insulating layer **605** surrounding the capacitor structure **622**. The hybrid film stack **510** formed as the capacitor layer **620** in the capacitor structure **622** may

have a bottom surface in contact with the lower gate insulating layer **605** as needed. The interlayer insulator **624** may be in a single layer form, as depicted in FIG. **6B**, or in multiple layer form as needed.

It is noted that the hybrid film stack **510** formed by the process **400** may be utilized to form the capacitor layer **620**, gate insulating layer **605**, as indicated in the circles of FIG. **6B**, a passivation layer or any other suitable layers that require insulating materials in the TFT device structures **650** including LTPS TFT for LCD or OLED TFT as needed.

It is noted that the upper electrode **611** and the lower electrode **609** utilized to form the capacitor structures **622**, **613** may also be pixel electrodes and/or common electrodes as needed.

FIG. **7** depicts a simple capacitor structure **702** (e.g., a MIM (metal-insulating-metal) structure) that may be formed on the substrate **102** utilized in display devices. Similar the upper electrode **611** and the lower electrode **609**, (or a pixel electrode and a common electrode in a TFT device structure), the capacitor structure **702** includes a top electrode **704** and a bottom electrode **708** having the hybrid film stack **510** as a capacitor layer disposed in between to form the capacitor structure **702**. The capacitor layer comprises a high-k material comprising  $ZrO_2$  with or without aluminum dopants and an aluminum oxide layer as an interface layer. The hybrid film stack **510** serving as a capacitor layer in a capacitor structure may also in form of any numbers of the layers as needed.

FIG. **8** depicts yet another example of a TFT device structure **850**. Similar to the structure described above, the TFT device structure **850** includes a regular interlayer insulator **820** disposed on the gate electrode **614**. A passivation layer **822** may be formed on the interlayer insulator **820**. Another portion of the source and drain region **902** (electrically connected to the source and drain region **609a**, **609b**) is shown on the optional insulating layer **604**. Another portion of the source-drain metal electrode layer **810** (electrically connected to the source-drain metal electrode layer **610a**, **610b**) is disposed on and electrically coupled to the source and drain region **902**. A pixel electrode **808** may be electrically connected to the source-drain metal electrode layer **810**, **610a**, **610b**. In this particular example, a portion of a gate insulating layer **605** passes through and between the gate electrode **614** and the channel region **608**, extending to the area above the source and drain region **902**. In one example, the gate insulating layer **605** may be the hybrid film stack **510** formed using the process **400** described above with referenced to FIG. **4**. An additional electrode **804** is formed above the source and drain region **802** and the gate insulating layer **605**, forming a capacitor structure **806** in the device structure **850**. The additional electrode **804** formed on the gate insulating layer **605** (now also serves as a capacitor layer) may be electrically connected to the gate electrode **614**. Thus, the additional electrode **804** and the source and drain region **902** along with the gate insulating layer **605** formed therebetween form the capacitor structure **806** in the device structure **850**. Similarly, the gate insulating layer **605**, now also serves as a capacitor layer, may be similar to the capacitor layer **612** described above and may be in form of any of the layers as needed.

It is noted that the source-drain metal electrode layer **610a**, **610b**, **810**, the pixel electrode **808**, the common electrode, the gate electrode **614**, the upper electrode **611**, the lower electrode **609**, the top electrode **704**, the bottom electrode **708**, additional electrode **804** and any electrodes in the device structures may be any suitable metallic materials, including transparent conductive oxide layer (such as ITO or

the like), silver nano ink, carbon nano tube (CNT), silver nano ink and CNT, graphene, aluminum (Al), tungsten (W), chromium (Cr), tantalum (Ta), molybdenum (Mo), copper (Cu), TiN, MoO<sub>2</sub>, MoN<sub>x</sub>, combination thereof or any suitable materials.

It is noted that the structures above the passivation layer **822** or the planarization layer **615** are eliminated for sake of brevity. However, in some exemplary device structures, an additional OLED or LCD devices, or other suitable devices may be formed above the passivation layer **822** or the planarization layer **615** to form other suitable flexible mobile display devices, such as LTPS OLED display devices with touch screen panels as needed.

Thus, the methods described herein advantageously improve the electron stability, electrical performance, low leakage and good film stack integration of display device structures by controlling the materials, particular a hybrid film stack having a high-k material comprising Zr containing layer formed on an interface layer comprising aluminum containing layer. The hybrid film stack may be fabricated either an ALD or PE-ALD and/or PECVD process, and structures of a gate insulating layer, capacitor layer, inter-layer insulator, passivation layer, insulating materials in the display devices, along with a dielectric layer formed as a capacitor in the display devices with desired high electrical performance.

While the foregoing is directed to embodiments of the present disclosure, other and further embodiments of the disclosure may be devised without departing from the basic scope thereof, and the scope thereof is determined by the claims that follow.

What is claimed is:

1. A thin film transistor structure comprising:
  - gate, source and drain electrodes formed in a thin film transistor on a transparent substrate;
  - a silicon containing insulating layer formed in direct contact with the transparent substrate, the silicon containing insulating layer disposed below the gate, source and drain electrodes;
  - an insulating layer formed in direct contact with the silicon containing insulating layer, wherein the insulating layer is disposed below the gate electrode; and
  - a capacitor layer formed in direct contact with the gate electrode and the insulating layer, wherein the capacitor layer comprises a hybrid film stack having an interface layer disposed between a dielectric layer and a top layer, the dielectric layer comprising an amorphous aluminum doped zirconium containing material, wherein the dielectric layer has a thickness of 250 Å to 900 Å and a current leakage of less than 1E-8 A/cm<sup>2</sup>, wherein the interface layer is at least one of aluminum oxide (Al<sub>2</sub>O<sub>3</sub>), aluminum nitride (AlN), aluminum titanium oxide (AlTiO), aluminum zirconium oxide (AlZrO), aluminum oxynitride (AlON), or yttrium oxide (Y<sub>2</sub>O<sub>3</sub>).
2. The structure of claim 1, wherein the dielectric layer comprises a dielectric constant greater than 15 and less than 25.
3. The structure of claim 1, wherein the top layer is disposed directly on the interface layer of the hybrid film stack, and the top layer comprises a silicon containing material.
4. The structure of claim 3, wherein the silicon containing material is silicon oxide or silicon nitride.

5. The structure of claim 1, wherein the dielectric layer is an aluminum doped ZrO<sub>2</sub> layer.

6. The structure of claim 1, where the amorphous aluminum doped zirconium containing material has an aluminum concentration between about 6 atm. % and about 20 atm. %.

7. The structure of claim 1, wherein the dielectric layer or the interface layer is formed by an ALD process or a PE-ALD process.

8. The structure of claim 1, wherein the insulating layer comprises the hybrid film stack.

9. A device structure utilized for display devices, comprising:

- a capacitor structure comprising a lower electrode, an upper electrode, and a hybrid film stack formed between the lower and the upper electrode, wherein the lower electrode is in direct contact with an insulating layer, the insulating layer in direct contact with a silicon-containing insulating layer, wherein the silicon-containing insulating layer is formed in direct contact with a transparent substrate, wherein the hybrid film stack comprises an interface layer disposed on and in direct contact with an aluminum doped Zr containing layer, the aluminum doped Zr containing layer having a dielectric constant between 15 and 25, wherein the aluminum doped Zr containing layer has a thickness of 250 Å to 900 Å and a current leakage of less than 1E-8 A/cm<sup>2</sup>, wherein the interface layer is at least one of aluminum oxide (Al<sub>2</sub>O<sub>3</sub>), aluminum nitride (AlN), aluminum titanium oxide (AlTiO), aluminum zirconium oxide (AlZrO), aluminum oxynitride (AlON), or yttrium oxide (Y<sub>2</sub>O<sub>3</sub>); and

wherein a silicon containing layer is disposed directly on the interface layer in the hybrid film stack.

10. The device structure of claim 9, wherein the insulating layer comprises the hybrid film stack, wherein the insulating layer is disposed below the two electrodes.

11. A device structure, comprising:

- a thin film transistor structure comprising source, drain, and gate electrodes formed over a silicon containing insulating layer; and
- a capacitor structure comprising top and bottom electrodes, and a hybrid film stack between the top and bottom electrodes, wherein the capacitor structure is formed over the silicon containing insulating layer, the silicon containing insulating layer is formed in direct contact with a substrate, wherein an insulating layer formed in direct contact with the silicon containing insulating layer, and below the gate electrode, and wherein a capacitor layer is formed directly on the gate electrode and the insulating layer, wherein the capacitor layer extends between top and bottom electrodes of the capacitor structure, wherein the capacitor layer comprises a hybrid film stack having an interface layer disposed between and in direct contact with a dielectric layer and a top layer comprising a silicon-containing material, the dielectric layer comprising an amorphous aluminum doped zirconium containing material, wherein the interface layer is at least one of aluminum oxide (Al<sub>2</sub>O<sub>3</sub>), aluminum nitride (AlN), aluminum titanium oxide (AlTiO), aluminum zirconium oxide (AlZrO), aluminum oxynitride (AlON), or yttrium oxide (Y<sub>2</sub>O<sub>3</sub>), wherein the dielectric layer has a thickness of 250 Å to 900 Å and a current leakage of less than 1E-8 A/cm<sup>2</sup>.